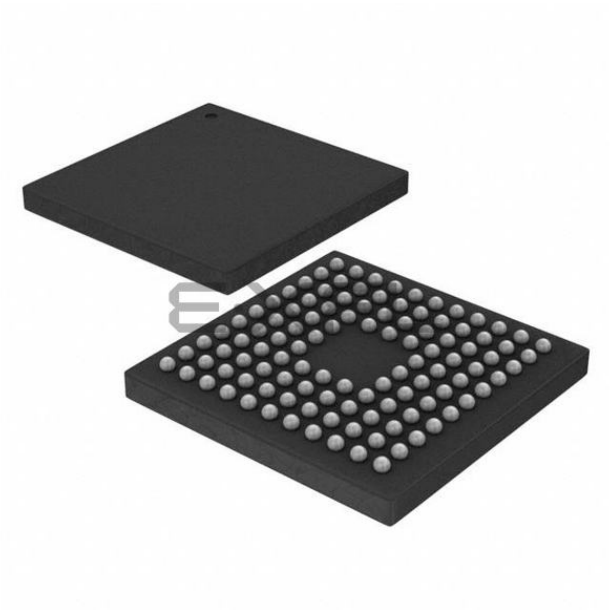

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	90
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-LFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg290f128-bga112

2.1.27 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE^{TM}), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG290 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32WG290, there are 90 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32WG290 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA

Module	Configuration	Pin Connections
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNC, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNC, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	90 pins	Available pins are shown in Table 4.3 (p. 67)

2.3 Memory Map

The *EFM32WG290* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		3.0[1]	4.0[1]	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.65	1.3	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.65	4.0	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.055	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.44	0.9	µA

[1]Using backup RTC.

3.4.1 EM1 Current Consumption

Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz

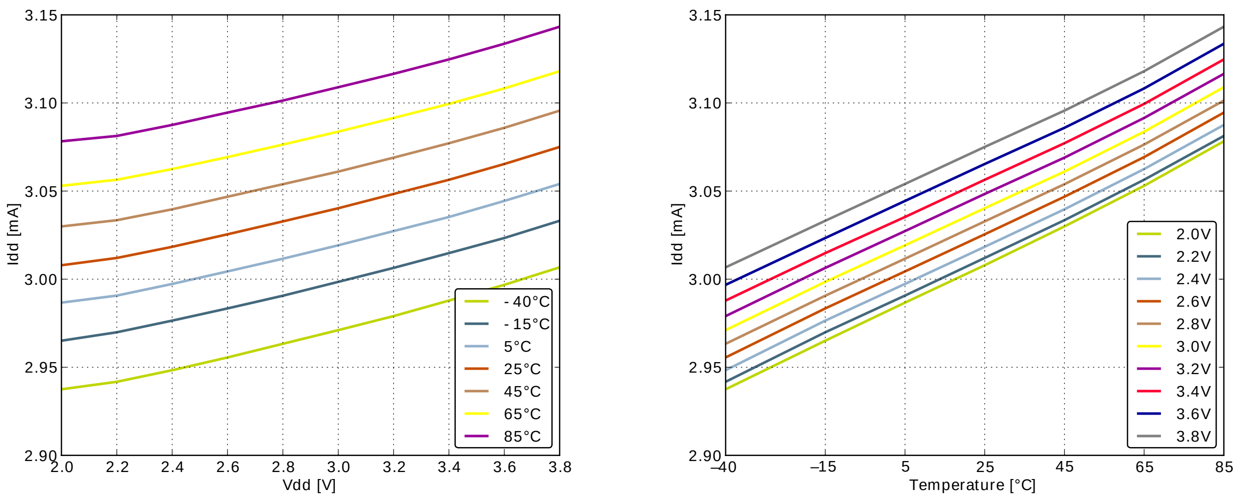


Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz

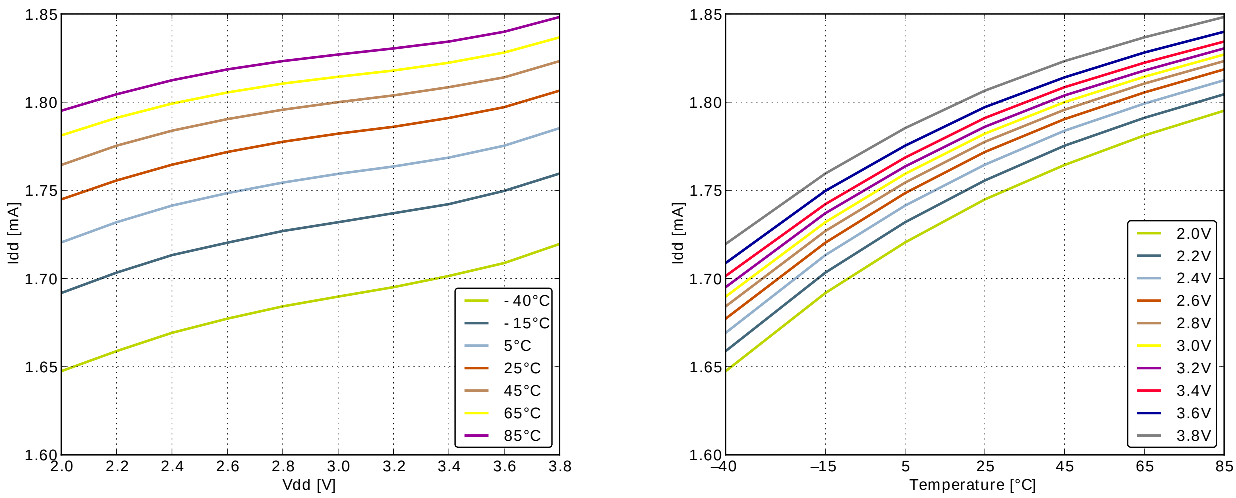
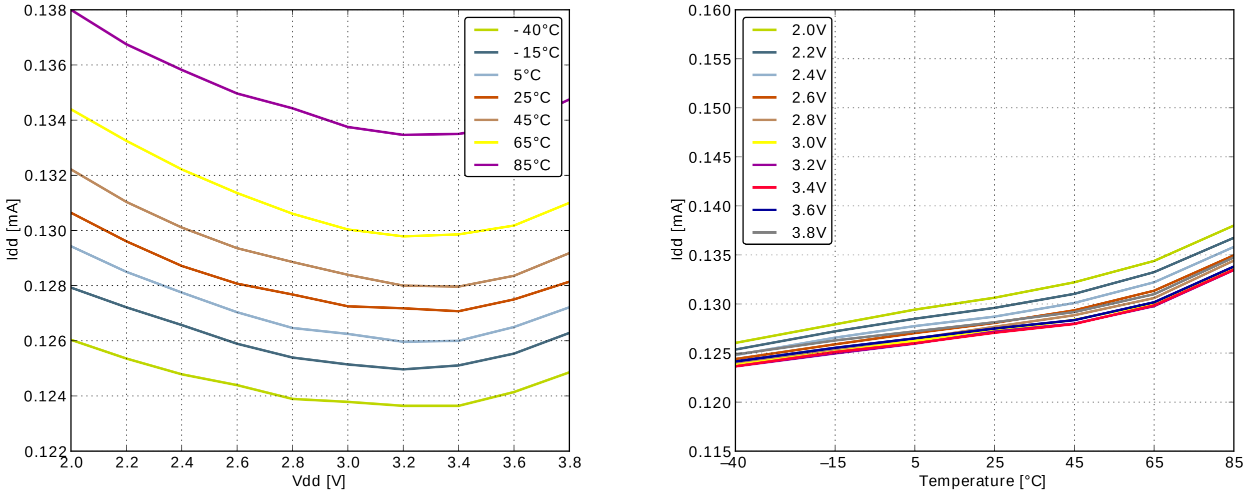
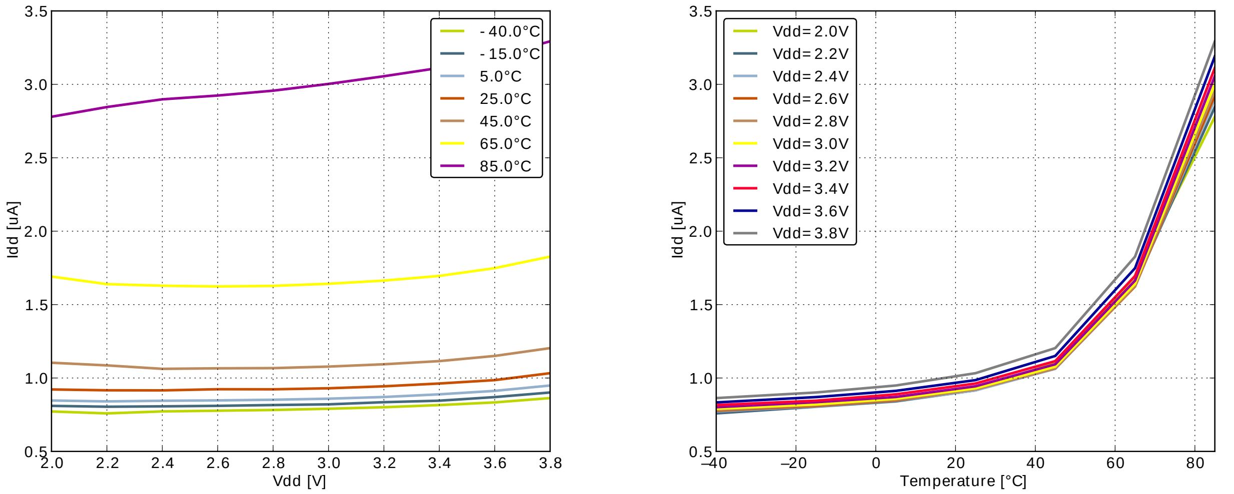


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 1.2MHz



3.4.2 EM2 Current Consumption

Figure 3.8. EM2 current consumption. RTC[1] prescaled to 1kHz, 32.768 kHz LFRCO.



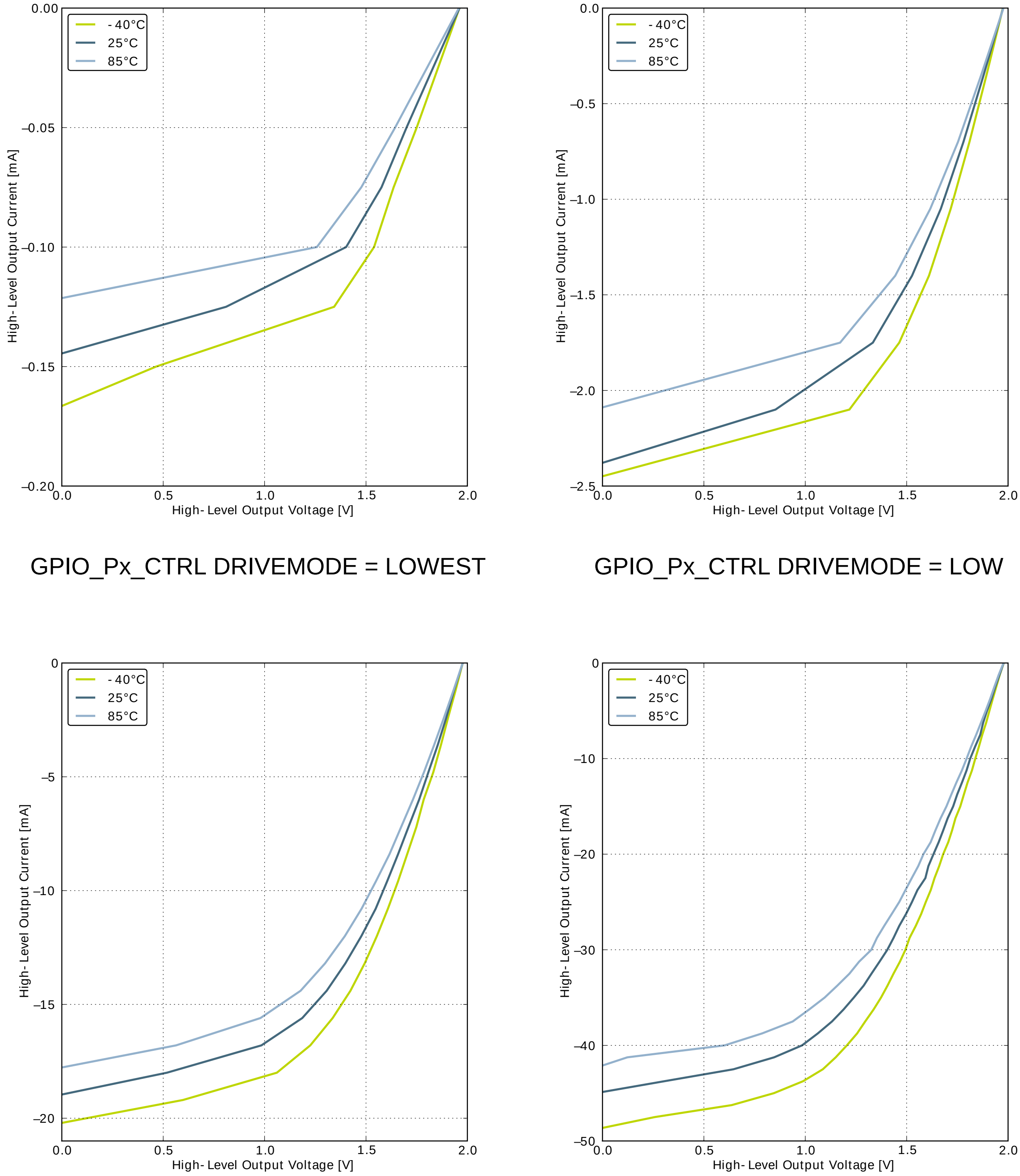
[1] Using backup RTC.

3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V

Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



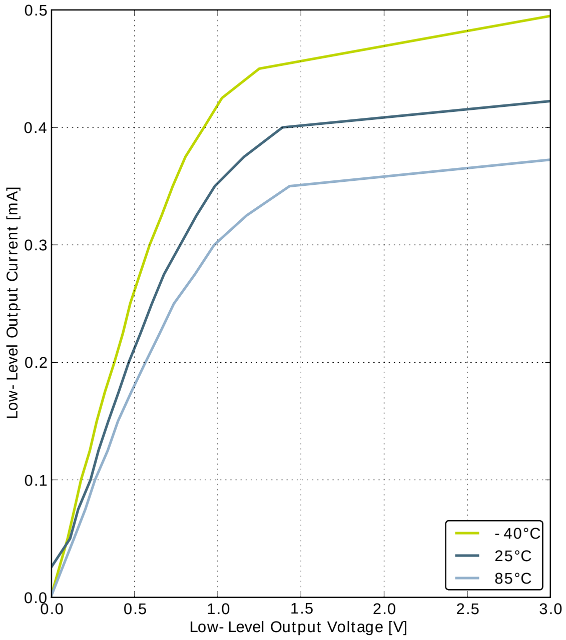
GPIO_Px_CTRL DRIVEMODE = LOWEST

GPIO_Px_CTRL DRIVEMODE = LOW

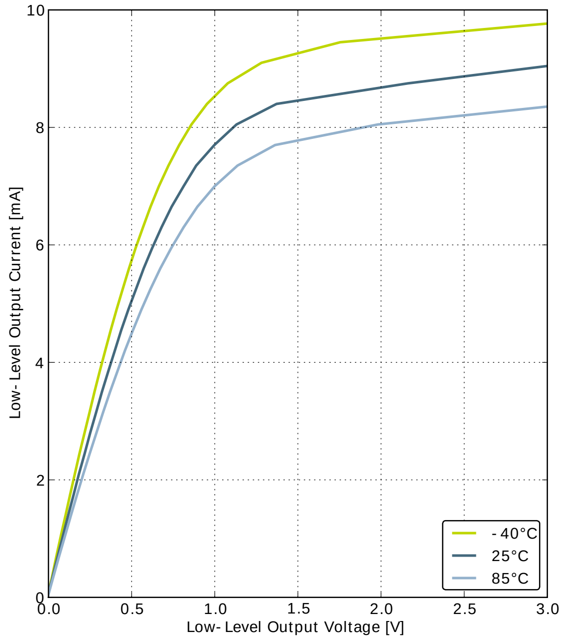
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH

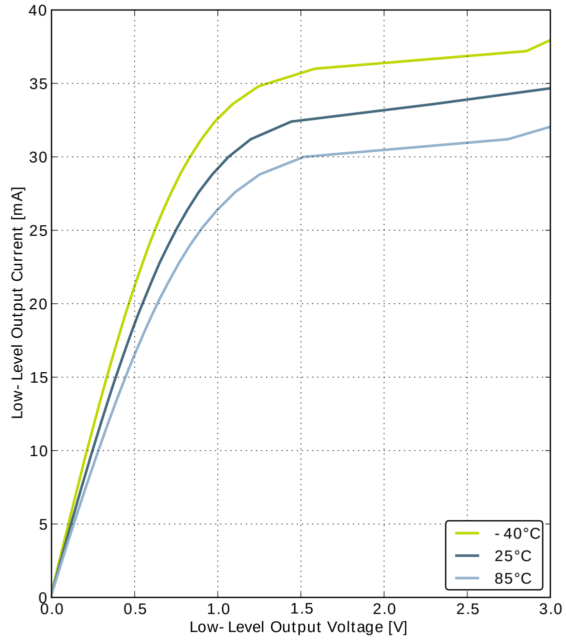
Figure 3.13. Typical Low-Level Output Current, 3V Supply Voltage



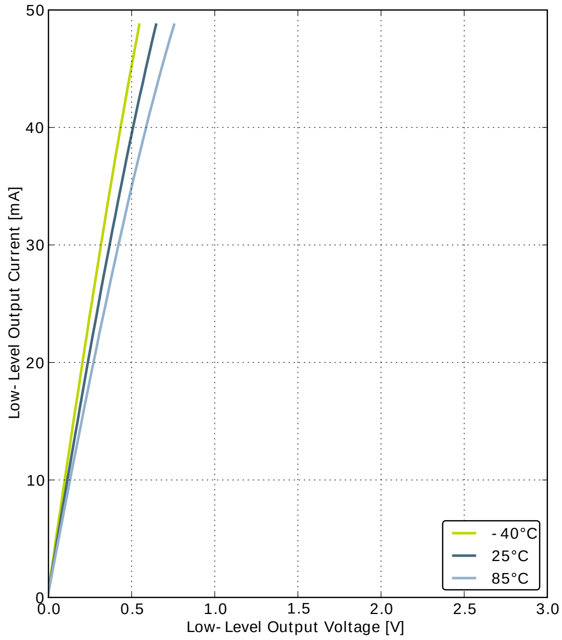
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

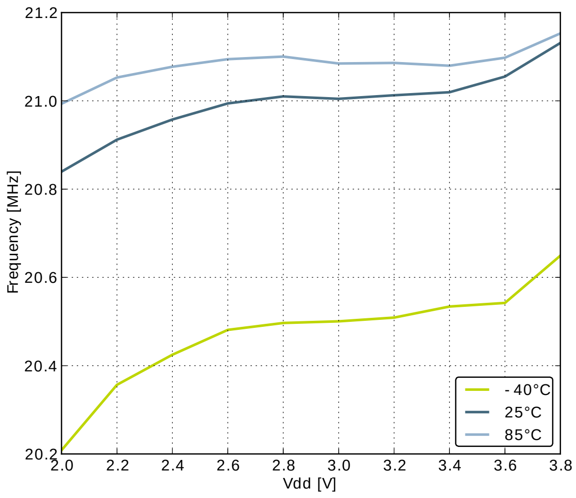


GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature



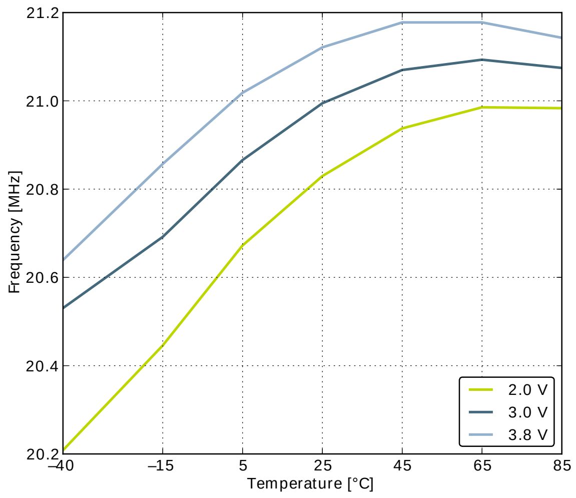
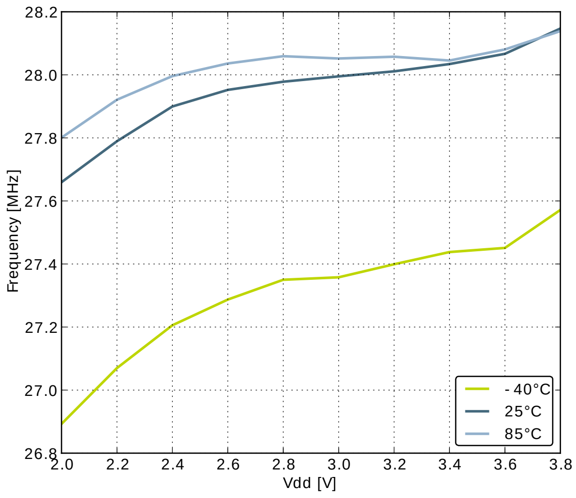
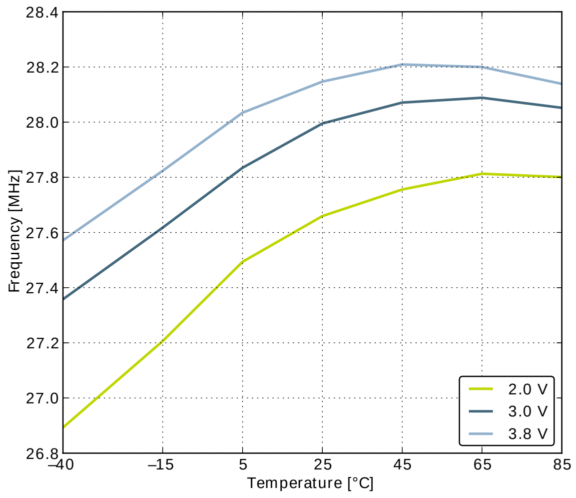


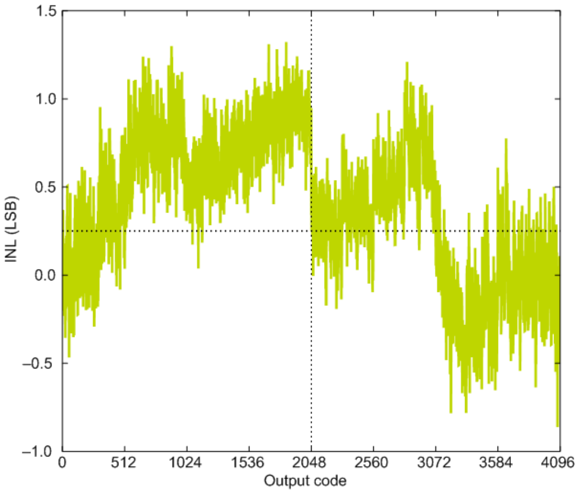
Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



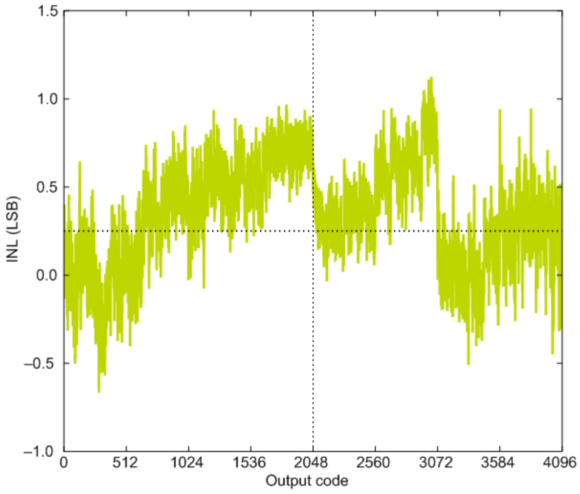


Symbol	Parameter	Condition	Min	Typ	Max	Unit
	erence voltage on channel 6					
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		µA
I_{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		µA
C_{ADCIN}	Input capacitance			2		pF
R_{ADCIN}	Input ON resistance		1			MOhm
$R_{ADCFILT}$	Input RC filter resistance			10		kOhm
$C_{ADCFILT}$	Input RC filter/decoupling capacitance			250		fF
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator			5		µs

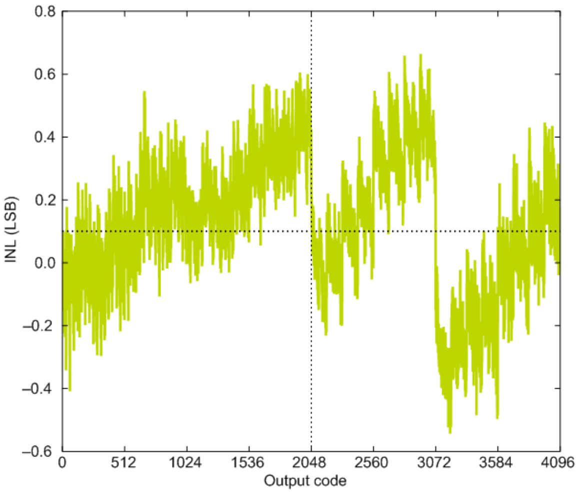
Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



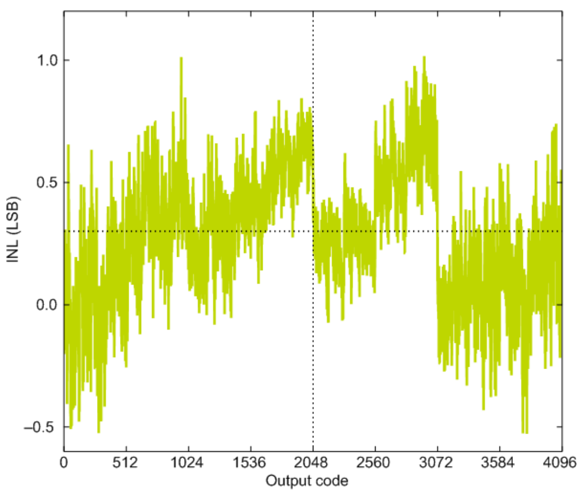
1.25V Reference



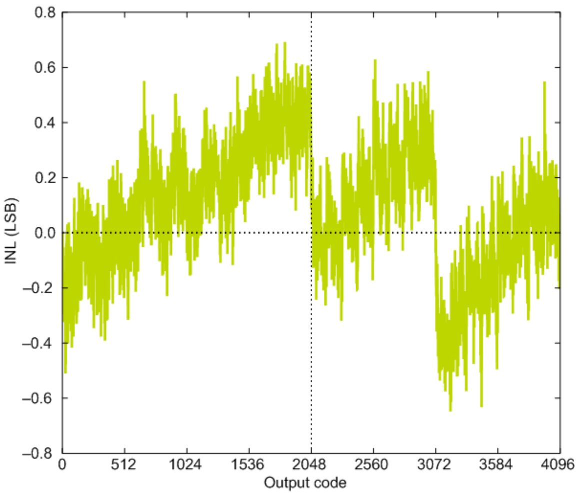
2.5V Reference



2XVDDVSS Reference

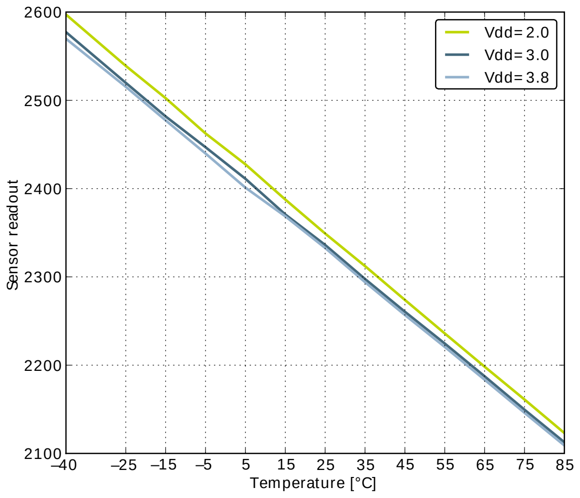


5VDIFF Reference



VDD Reference

Figure 3.31. ADC Temperature sensor readout



3.11 Digital Analog Converter (DAC)

Table 3.16. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400[1]		µA
		100 kSamples/s, 12 bit		200[1]		µA
		1 kSamples/s 12 bit NORMAL		17[1]		µA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cyckles per conversion			2		
$t_{DACCONV}$	Conversion time		2			µs
$t_{DACSETTLE}$	Settling time			5		µs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	µA
G_{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW_{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM_{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C_L=75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
R_{INPUT}	Input Resistance			100		Mohm
R_{LOAD}	Load Resistance		200			Ohm
I_{LOAD_DC}	DC Load Current				11	mA
V_{INPUT}	Input Voltage	OPAxHCMDIS=0	V_{SS}		V_{DD}	V
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, V_{SS}<V_{in}<V_{DD}, OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V_{SS}<V_{in}<$_{DD}$-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		µV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		µV_{RMS}

Figure 3.40. EBI Read Enable Related Output Timing

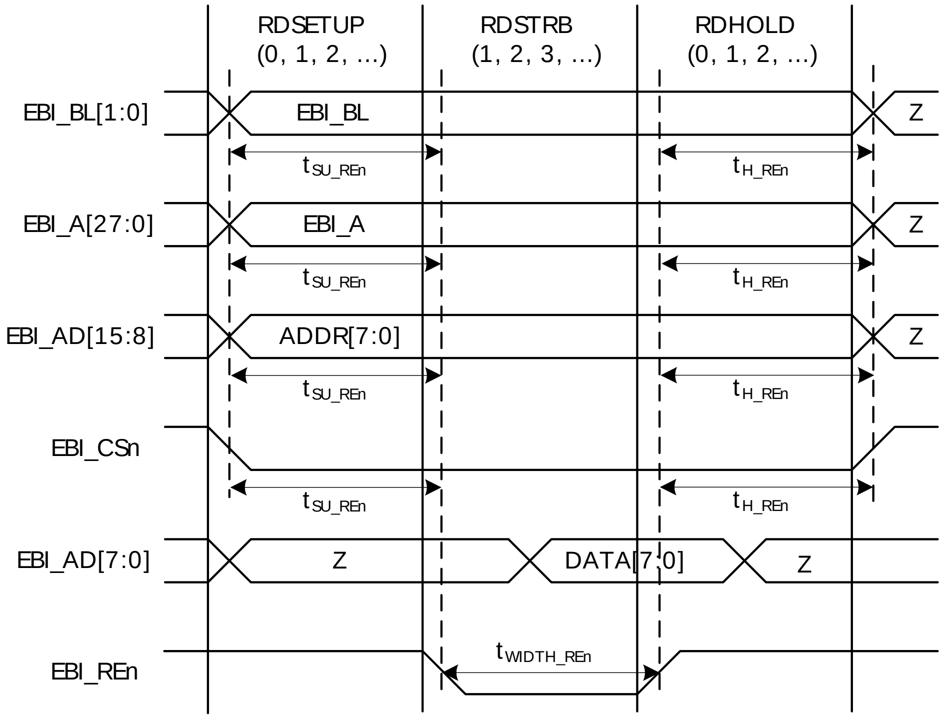


Table 3.22. EBI Read Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_REn} 1 2 3 4	Output hold time, from trailing EBI_REn/ EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-10.00 + (RDHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_REn} 1 2 3 4 5	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_REn/EBI_NANDREn edge	-10.00 + (RDSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_REn} 1 2 3 4 5 6	EBI_REn pulse width	-9.00 + ((RD-STRB+1) * $t_{HFCORECLK}$)			ns

[1]Applies for all addressing modes (figure only shows D8A8. Output timing for EBI_AD only applies to multiplexed addressing modes D8A24ALE and D16A16ALE)
[2]Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5]The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * $t_{HFCLKNODIV}$.
[6]When page mode is used, RDSTRB is replaced by RDPA for page hits.

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. BGA112 PCB Land Pattern

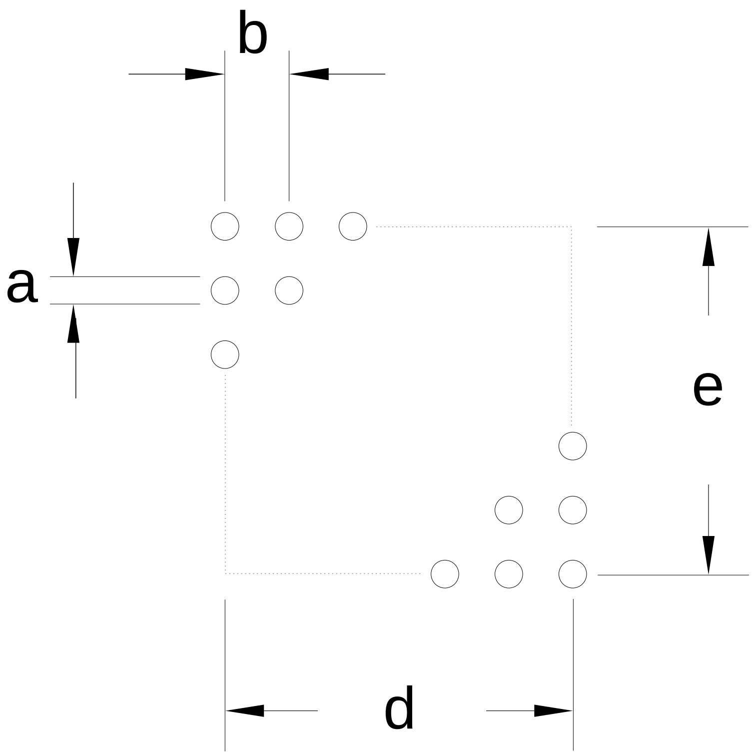


Table 5.1. BGA112 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.35
b	0.80
d	8.00
e	8.00

Figure 5.2. BGA112 PCB Solder Mask

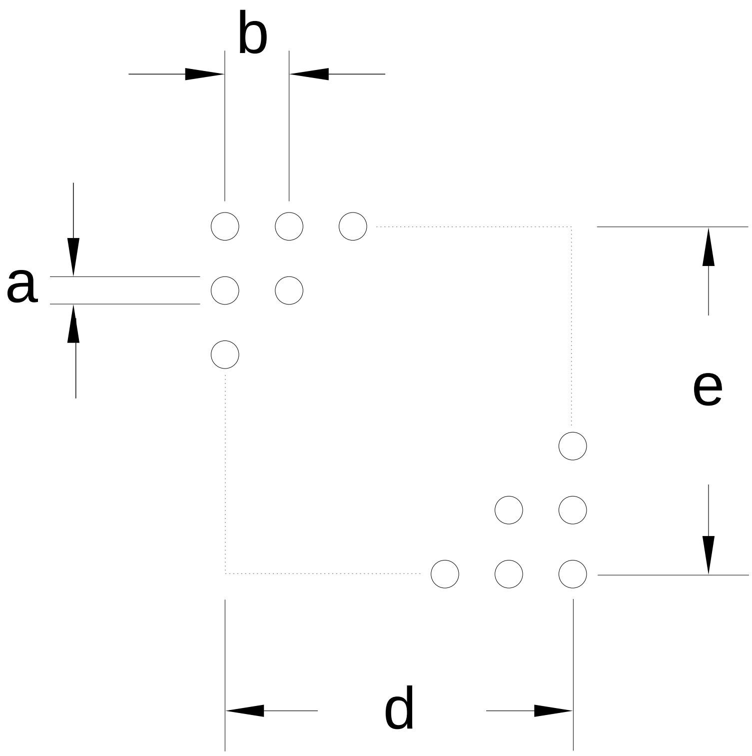


Table 5.2. BGA112 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.48
b	0.80
d	8.00
e	8.00

7 Revision History

7.1 Revision 1.40

June 13th, 2014

Removed "Preliminary" markings.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Added AUXHFRCO to blockdiagram and electrical characteristics.

Updated current consumption data.

Updated transition between energy modes data.

Updated power management data.

Updated GPIO data.

Updated LFRCO, HFRCO and ULFRCO data.

Updated ADC data.

Updated DAC data.

Updated OPAMP data.

Updated ACMP data.

Updated VCMP data.

Added EBI timing chapter.

7.2 Revision 1.31

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.3 Revision 1.30

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

B Contact Information

Silicon Laboratories Inc.
400 West Cesar Chavez
Austin, TX 78701

Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

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